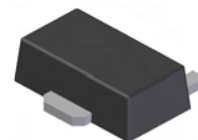


Features

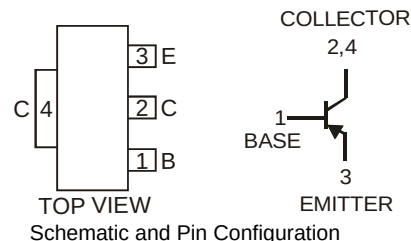
- Epitaxial Planar Die Construction
- Complementary NPN Type Available (DCX56)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free By Design/RoHS Compliant (Note 1)**
- "Green" Device (Note 2)



SOT89-3L

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish — Matte Tin annealed over Copper leadframe
(Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.072 grams (approximate)


 TOP VIEW
 Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-100	V
Collector-Emitter Voltage	V _{CEO}	-80	V
Emitter-Base Voltage	V _{EBO}	-5	V
Peak Pulse Current	I _{CM}	-1.5	A
Continuous Collector Current	I _C	-1	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P _D	1	W
Thermal Resistance, Junction to Ambient Air @ T _A = 25°C (Note 3)	R _{θJA}	125	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-100	—	—	V	I _C = -100μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-80	—	—	V	I _C = -10mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5	—	—	V	I _E = -10μA, I _C = 0
Collector Cutoff Current	I _{CBO}	—	—	-100 -20	nA μA	V _{CB} = -30V, I _E = 0 V _{CB} = -30V, I _E = 0, T _A = 150°C
Emitter Cutoff Current	I _{EBO}	—	—	-100	nA	V _{EB} = -5V, I _C = 0
ON CHARACTERISTICS (Note 4)						
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	—	-0.5	V	I _C = -500mA, I _B = -50mA
Base-Emitter Turn-On Voltage	V _{BE(SAT)}	—	—	-1.0	V	I _C = -500mA, V _{CE} = -2V
DC Current Gain	DCX53, DCX53-16	h _{FE}	63 40	— —	— —	I _C = -5mA, V _{CE} = -2V I _C = -500mA, V _{CE} = -2V
	DCX53		63	—	250	I _C = -150mA, V _{CE} = -2V
	DCX53-16		100	—	250	I _C = -150mA, V _{CE} = -2V
	SMALL SIGNAL CHARACTERISTICS					
Current Gain-Bandwidth Product	f _T	—	200	—	MHz	I _C = -50mA, V _{CE} = -5V, f = 100MHz
Output Capacitance	C _{obo}	—	—	25	pF	V _{CB} = -10V, f = 1MHz

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 4. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.

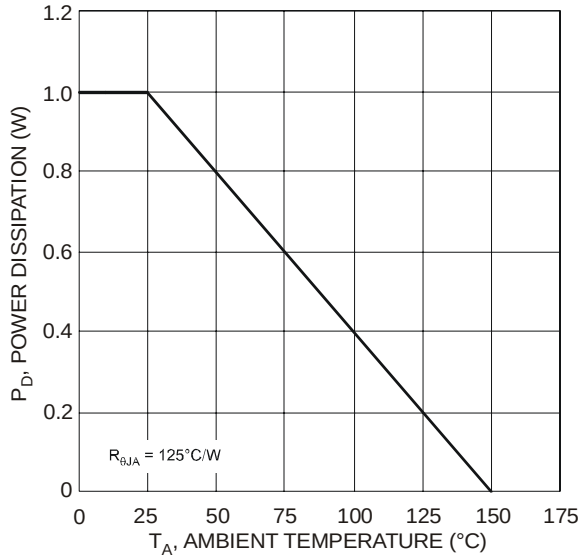


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

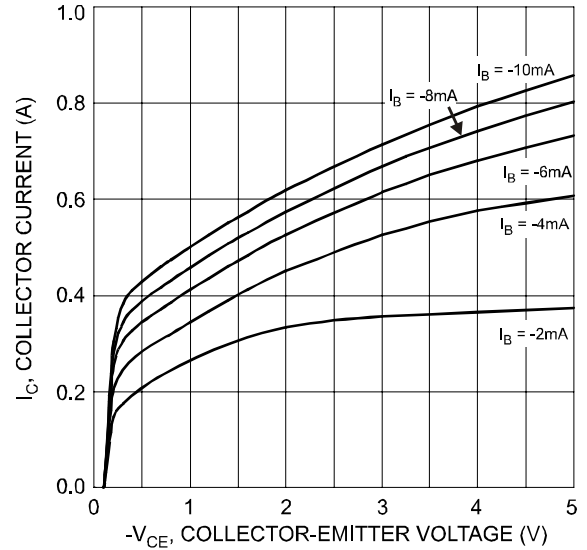


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

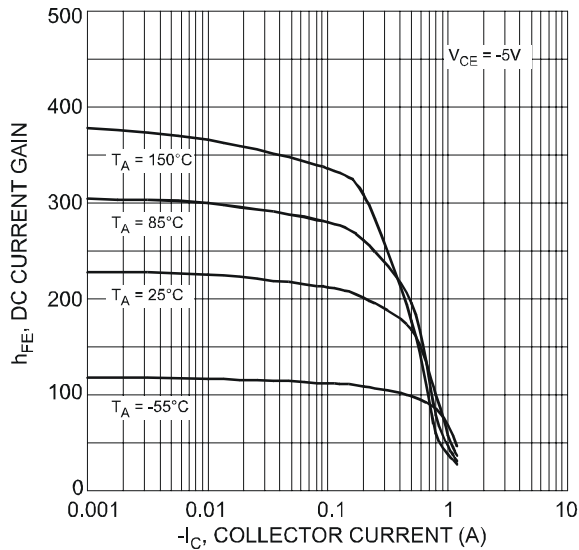


Fig. 3 Typical DC Current Gain vs. Collector Current

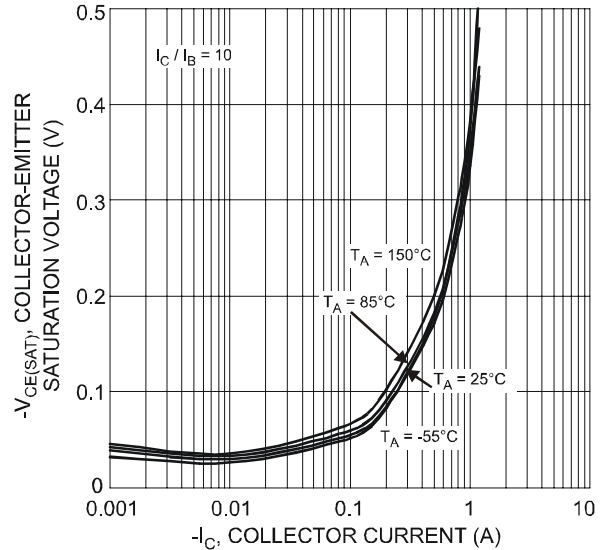


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

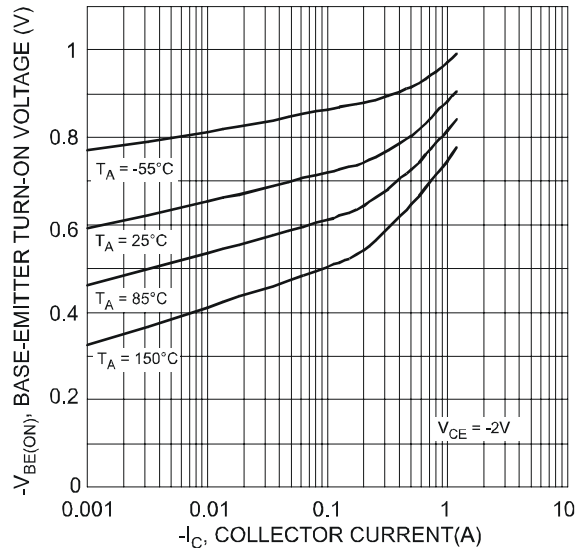


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

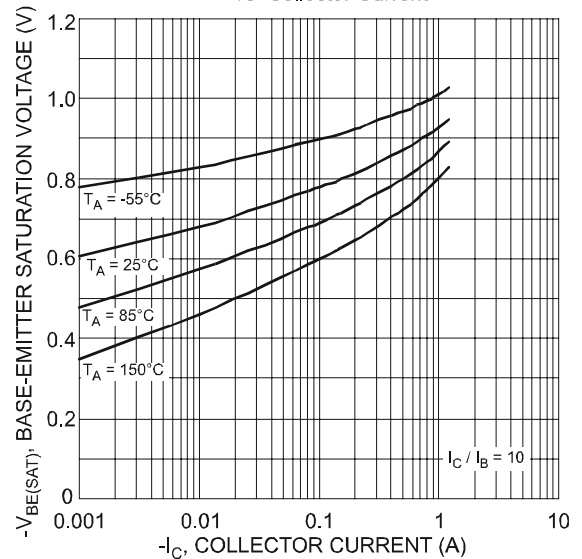


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

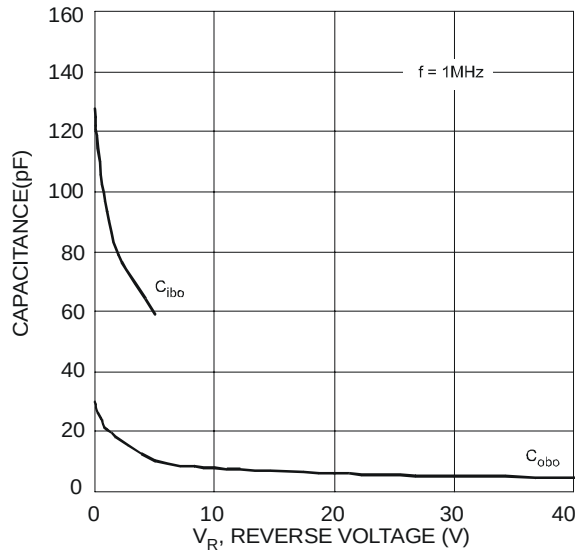


Fig. 7 Typical Capacitance Characteristics

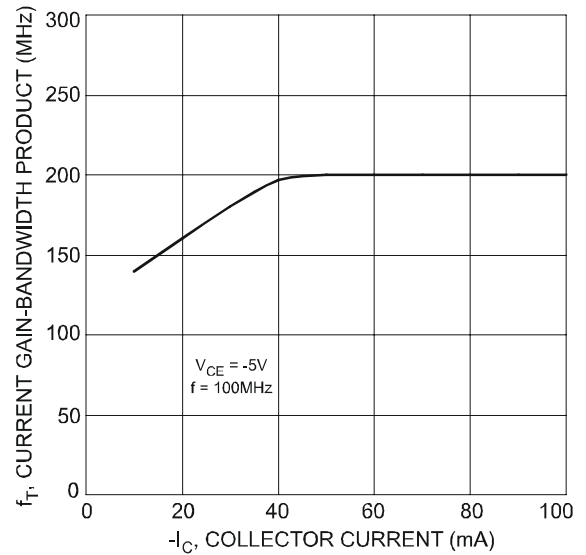


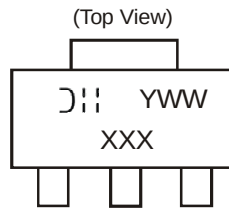
Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
DCX53-13	SOT89-3L	2500/Tape & Reel
DCX53-16-13	SOT89-3L	2500/Tape & Reel

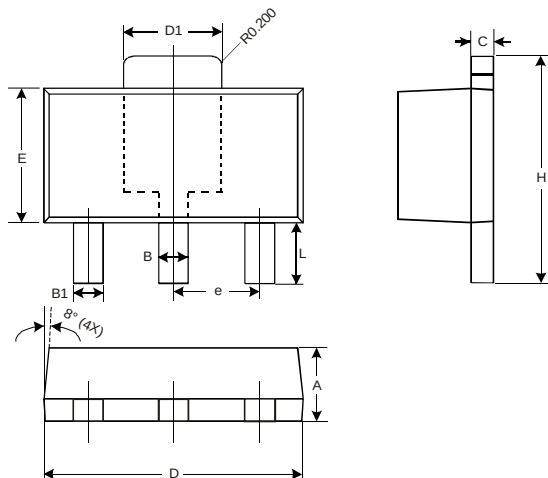
Notes: 5. For packaging details, go to our website at <http://www.diodes.com/ap02007.pdf>.

Marking Information



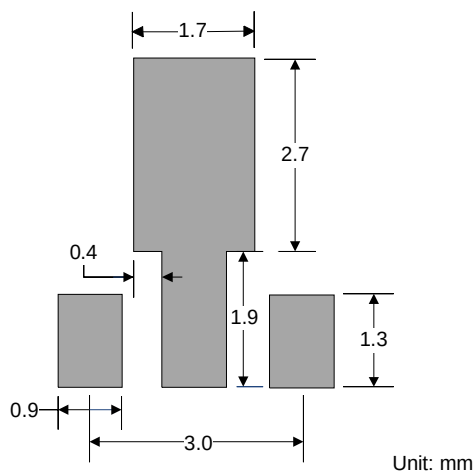
DII = Manufacturer's code marking
 XXX = Product type marking code Ex: P18 = DCX53
 P18-16 = DCX53 -16
 YWW = Date code marking
 Y = Last digit of year ex: 7 = 2007
 WW = Week code 01 - 52

Package Outline Dimensions



SOT89-3L			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.45	0.55	0.50
B1	0.37	0.47	0.42
C	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.50	1.70	1.60
E	2.40	2.60	2.50
e	—	—	1.50
H	3.95	4.25	4.10
L	0.90	1.20	1.05
All Dimensions in mm			

Suggested Pad Layout



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<http://moschip.ru/get-element>

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